

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

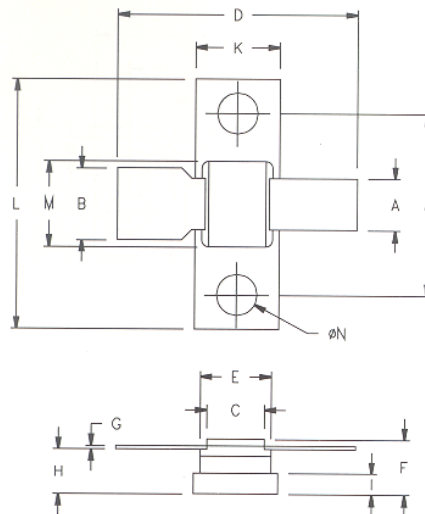
The **ASI SD1537-2** is a Common Base Device Class C, Designed for IFF Applications.

FEATURES INCLUDE:

- Gold Metelization
- InputMatching
- Broad Band Performance

MAXIMUM RATINGS

I_C	5.0 A
V_{CES}	50 V
P_{DISS}	300 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +150 °C
θ_{JC}	0.60 °C/W

PACKAGE STYLE .175 2L FLG


	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.165/4,19	.175/4,45	J	.560/14,22	.570/14,48
B	.215/5,46	.225/5,72	K	.245/6,22	.255/6,48
C	.175/4,45	.185/4,70	L	.740/18,80	.750/19,05
D	.740/18,80		M	.245/6,22	.255/6,48
E	.225/5,72	.235/5,97	N	.128/3,25	.132/3,35
F	.155/3,94	.175/4,45			
G	.003/0,08	.006/0,15			
H	.120/3,05	.135/3,43			
I	.058/1,47	.068/1,73			

CHARACTERISTICS T_C = 25°C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I _C = 15 mA	50			V
BV_{EBO}	I _E = 10 mA	4.0			V
h_{FE}	V _{CE} = 5.0 V I _C = 200 mA	10			---
P_{OUT}	V _{CC} = 43 V P _{IN} = 20 W f = 1090 MHz PULSE	150			W
G_P	WIDTH = 10 μS DUTY CYCLE = 1.0%	8.7			dB
η_C		35			%